

**Amendments to the Specification**

Please replace the paragraph beginning at page 13, line 11 of the Specification with the following paragraph:

Moreover, the buffer **13** may be doped with deep acceptors as described in S. Heikman *et al.*, Growth of Fe-Doped Semi-insulating GaN by Metalorganic Chemical Vapor Deposition, Appl. Phys. Let. 81, pp. 439-441 (2002). Specific examples of co-doped layers are provided in U.S. Patent Application Serial No. 10/752,970 entitled

15 "Co-Doping for Fermi Level Control in Semi-Insulating Group III Nitrides," filed January 7, 2004 and assigned to the assignee of the present invention, the disclosure of which is incorporated herein by reference. The buffer could be doped with Fe or another deep acceptor.